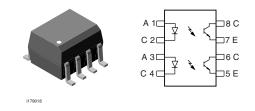


Vishay Semiconductors

## Optocoupler, Phototransistor Output, Dual Channel, SOIC-8 package



#### DESCRIPTION

The ILD205T/206T/207T/211T/213T/217T are optically coupled pairs with a Gallium Arsenide infrared LED and a silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. The ILD205T/206T/207T/211T/213T/217T come in a standard SOIC-8 small outline package for surface mounting which makes it ideally suited for high density applications with limited space. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

A specified minimum and maximum CTR allows a narrow tolerance in the electrical design of the adjacent circuits. The high  $BV_{CEO}$  of 70 V gives a higher safety margin compared to the industry standard of 30 V.

#### FEATURES

- Two Channel Coupler
- SOIC-8 Surface Mountable Package
- Standard Lead Spacing of 0.05"
- Available only on Tape and Reel Option (Conforms to EIA Standard 481-2)



- BoHS
- COMPLIANT
- Isolation Test Voltage, 4000 V<sub>RMS</sub>
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### AGENCY APPROVALS

- UL1577, File No. E52744 System Code Y
- CUL File No. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-2 (VDE0884) Available with Option 1

ORDER INFORMATION						
PART	REMARKS					
ILD205T	CTR 40 - 80 %, SOIC-8					
ILD206T	CTR 63 - 125 %, SOIC-8					
ILD207T	CTR 100 - 200 %, SOIC-8					
ILD211T	CTR > 20 %, SOIC-8					
ILD213T	CTR > 100 %, SOIC-8					
ILD217T	CTR > 100 %, SOIC-8					

Note:

For additional information on the available options refer to Option Information.

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PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Peak reverse voltage		V <sub>R</sub>	6.0	V
Peak pulsed current	1.0 μs, 300 pps		1.0	А
Continuous forward current per channel			30	mA
Power dissipation		P <sub>diss</sub>	50	mW
Derate linearly from 25 °C			0.66	mW/°C
OUTPUT				
Collector-emitter breakdown voltage		BV <sub>CEO</sub>	70	V
Emitter-collector breakdown voltage		BV <sub>ECO</sub>	7.0	V
Power dissipation per channel		P <sub>diss</sub>	125	mW
Derate linearly from 25 °C			1.67	mW/°C
COUPLER			· · · · ·	
Isolation test voltage	t = 1.0 s	V <sub>ISO</sub>	4000	V <sub>RMS</sub>
Total package dissipation ambient (2 LEDs + 2 detectors, 2 channels)		P <sub>tot</sub>	300	mW
Derate linearly from 25 °C			4.0	mW/°C
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C
Operating temperature		T <sub>amb</sub>	- 55 to + 100	°C
Soldering time from 260 °C		T <sub>sld</sub>	10	sec.

#### Note:

<sup>1)</sup>  $T_{amb} = 25 \,^{\circ}C$ , unless otherwise specified.

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS <sup>1)</sup>								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN	TYP.	MAX	UNIT	
INPUT								
Forward voltage	I <sub>F</sub> = 10 mA		V <sub>F</sub>		1.2	1.55	V	
Reverse current	V <sub>R</sub> = 6.0 V		I <sub>R</sub>		0.1	100	μΑ	
Capacitance	V <sub>R</sub> = 0		C <sub>O</sub>		25		pF	
OUTPUT								
Collector-emitter breakdown voltage	I <sub>C</sub> = 10 μA		BV <sub>CEO</sub>	70			V	
Emitter-collector breakdown voltage	I <sub>E</sub> = 10 μA		BV <sub>ECO</sub>	7.0			V	
Collector-emitter leakage current	$V_{CE} = 10 \text{ V}, \text{ I}_{F} = 0$		I <sub>CEO</sub>		5.0	50	nA	
Collector-emitter capacitance	$V_{CE} = 0$		C <sub>CE</sub>		10		pF	
COUPLER								
Collector-emitter saturation voltage	$I_{\rm F} = 10 \text{ mA}, I_{\rm C} = 2.5 \text{ mA}$		V <sub>CE(sat)</sub>			0.4	V	
Capacitance (input-output)			C <sub>IO</sub>		0.5		pF	
Resistance, input to output			R <sub>IO</sub>		100		GΩ	

Note:

 $^{1)}$  T<sub>amb</sub> = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



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CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYPE	MAX	UNIT	
	V <sub>CE</sub> = 5.0 V, I <sub>F</sub> = 10 mA	ILD205T	CTR <sub>DC</sub>	40		80	%	
		ILD206T	CTR <sub>DC</sub>	63		125	%	
DC Current Transfer Ratio		ILD207T	CTR <sub>DC</sub>	100		200	%	
		ILD211T	CTR <sub>DC</sub>	20			%	
		ILD213T	CTR <sub>DC</sub>	100			%	
	V <sub>CE</sub> = 5.0 V, I <sub>F</sub> = 1.0 mA	ILD205T	CTR <sub>DC</sub>	13	30		%	
		ILD206T	CTR <sub>DC</sub>	22	45		%	
		ILD207T	CTR <sub>DC</sub>	34	70		%	
		ILD217T	CTR <sub>DC</sub>	100	120		%	

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYPE	MAX	UNIT
Turn-on time	$I_{C}$ = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 5.0 V		t <sub>on</sub>	5.0			μs
Turn-off time	$I_{C}$ = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 5.0 V		t <sub>off</sub>	4.0			μs

SAFETY AND INSULATION RATINGS <sup>1)</sup>							
PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP.	МАХ	UNIT	
Climatic classification (according to IEC 68 part 1)				55/100/21			
Comparative tracking index		CTI	175		399		
V <sub>IOTM</sub>			6000			V	
V <sub>IORM</sub>			560			V	
P <sub>SO</sub>					350	mW	
I <sub>SI</sub>					150	mA	
T <sub>SI</sub>					165	°C	
Creepage			4			mm	
Clearance			4			mm	
Insulation thickness, reinforced rated	per IEC60950 2.10.5.1		0.2			mm	

Note: <sup>1)</sup> As per IEC60747-5-2, §7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.



### **Vishay Semiconductors**

#### **TYPICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

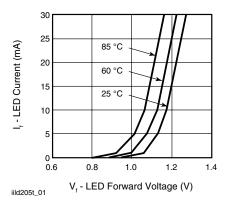
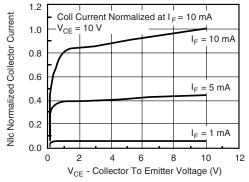


Figure 1. Forward Current vs. Forward Voltage



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Figure 2. Collector-Emitter Current vs. Temperature

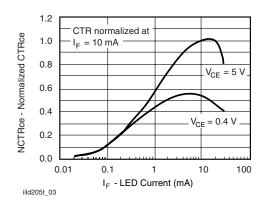


Figure 3. Normalized CTR<sub>ce</sub> vs. Forward Current

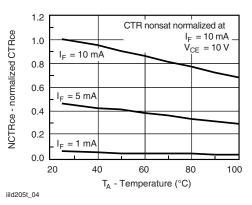


Figure 4. Current Transfer Ratio (normalized) vs. Ambient Temperature

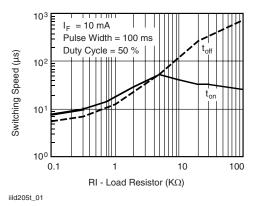


Figure 5. Switching Speed vs. Load Resistor

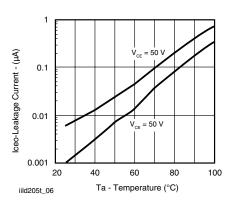
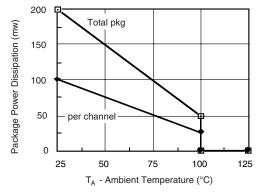


Figure 6. Collector Current vs. Ambient Temperature



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Figure 7. Power Dissipation vs. Ambient Temperature

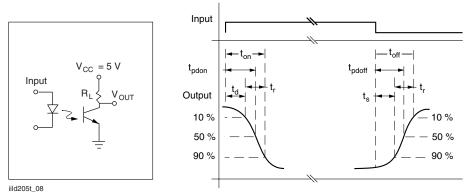
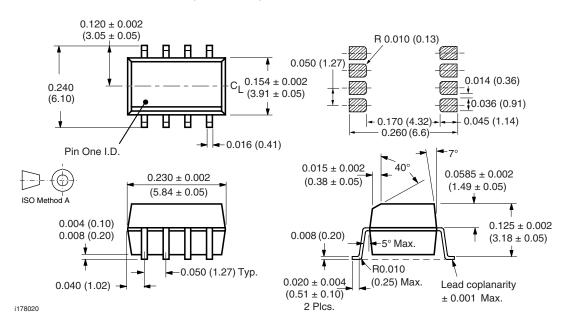


Figure 8. Switching Test Circuit

#### **PACKAGE DIMENSIONS** in inches (millimeters)



### Vishay Semiconductors

#### **Ozone Depleting Substances Policy Statement**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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